TPS7A14 1A、低入出力電圧、超低ドロップアウト・レギュレータ

1 特長

- 非常に低い入力電圧範囲:0.7V～2.2V
- 高効率:
  - 1A でのドロップアウト電圧:70mV (最大値、YBK)
  - V_{IN} = V_{OUT} + 100mV で仕様規定
- 非常に優れた負荷過渡応答:
  - 20mV (I_{LOAD} が 3mA から 600mA まで 20µs で変化する場合)
- 精度 (負荷、ライン、温度変動を含む):1%
- 高 PSRR:
  - 80dB (1kHz 時) (V_{OUT} = 0.8V、I_{OUT} = 500mA)
- 固定出力電圧で提供:
  - 0.5V～2.0V (25mV 刻み)
- V_{BIAS} 範囲:2.2V～5.5V
- パッケージ:
  - 6 ピン DSBGA:0.71mm × 1.16mm
  - 6 ピン WSON:2mm × 2mm
- アクティブ出力放電

2 アプリケーション

- カメラ・モジュール
- ワイヤレス・ヘッドホン / イヤホン
- スマートウォッチ、フィットネス・トラッカー
- スマートフォンおよびタブレット
- ポータブル医療機器
- ソリッド・ステート・ドライブ (SSD)

3 概要

TPS7A14 は、優れた過渡応答特性を持つ小型超低ドロップアウト・レギュレータ (LDO) です。このデバイスは 1A の電流を供給でき、AC 性能 (負荷およびライン過渡応答) が非常に優れています。入力電圧範囲は 0.7V～2.2V、出力電圧範囲は 0.5V～2.0V であり、負荷、ライン、温度範囲の全体にわたって 1% の非常に高い精度を維持します。

1 次側電源パスは IN ピンを経由し、最小で出力電圧を 50mV 上回る電圧の電源に接続できます。すべての電気的特性 (優れた出力電圧許容誤差、過渡応答、PSRR など) は、(出力電圧 + 100mV) の入力電圧に対して仕様規定されているため、実際に高い効率が得られます。このレギュレータは、外部から供給されるより高い V_{BIAS} レールを使って LDO の内部回路に電力を供給することで、極めて低い入力電圧に対応します。たとえば、IN ピンの電源電圧として高効率の DC/DC 降圧レギュレータの出力を使用でき、BIAS ピンの電源電圧として充電可能バッテリを使用できます。

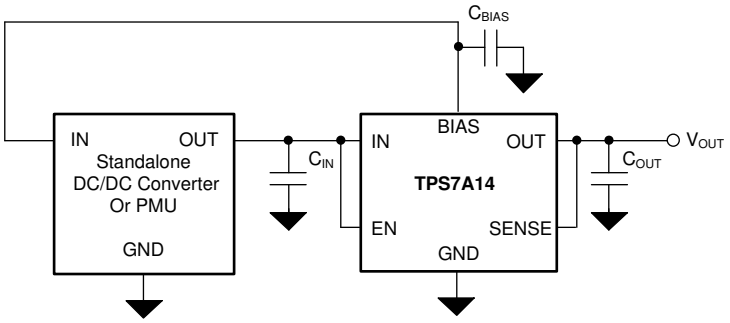
TPS7A14 には、ディスエーブル時に出力を高速放電するアクティブ・プルダウン回路が内蔵されており、既知のスタートアップ状態を確保できます。

TPS7A14 は 2mm × 2mm の 6 ピン WSON パッケージと、超小型の 0.71mm × 1.16mm、6 バンプ WCSP パッケージで供給されます。

パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイズ (2)
TPS7A14	YBK (WCSP、6)	1.16mm × 0.71mm
	DRV (WSON、6)	2mm × 2mm

(1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
(2) パッケージ・サイズ (長さ×幅) は公称値であり、該当する場合はピンも含まれます。



代表的なアプリケーション回路

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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (July 2023) to Revision D (August 2023) **Page**

- DRV (WSON) パッケージを「事前情報」から「量産データ」に変更 1
- Changed specifications for DRV package..... 6
- Added *Output Noise vs Frequency and* I_{OUT} curve for the DRV package..... 9
- Added *Recommended Layout (DRV Package)* figure..... 25

Changes from Revision B (May 2022) to Revision C (July 2023) **Page**

- 「事前情報」として、DRV (WSON) パッケージをドキュメントに追加 1
- 文書全体にわたって、固定出力電圧を「0.5V～2.05V」から「0.5V～2.0V」に変更 1
- 「概要」セクションの最後の段落でパッケージの説明を変更 1

5 Pin Configuration and Functions

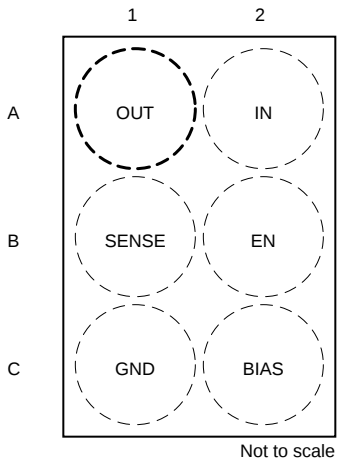


図 5-1. YBK Package, 6-Pin WCSP (Top View)

表 5-1. Pin Functions: YBK Package

PIN		TYPE	DESCRIPTION
NO.	NAME		
A1	OUT	Output	Regulated output pin. A 2.2-µF or greater capacitance is required from OUT to ground for stability. For best transient response, use an 8-µF (nominal) or larger ceramic capacitor from OUT to ground. Place the output capacitor as close to OUT as possible.
A2	IN	Input	Input pin. A 0.75-µF or greater capacitance is required from IN to ground for stability. Place the input capacitor as close to IN as possible.
B1	SENSE	Input	SENSE input. This pin is a feedback input to the regulator for SENSE connections. Connecting SENSE to the load helps eliminate voltage errors resulting from trace resistance between OUT and the load.
B2	EN	Input	Enable pin. Driving this pin to logic high enables the LDO. Driving this pin to logic low disables the LDO. If enable functionality is not required, EN must be connected to IN or BIAS.
C1	GND	—	Ground pin. This pin must be connected to ground.
C2	BIAS	Input	BIAS pin. This pin enables operation in low-input voltage, low-output voltage (LILO) conditions. For best performance, use 0.47-µF or larger ceramic capacitor from BIAS to ground. Place the bias capacitor as close to BIAS as possible.

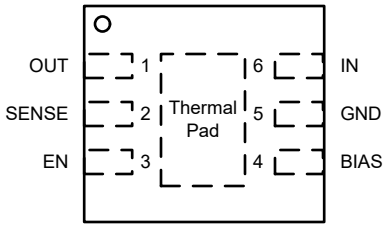


図 5-2. DRV Package, 6-Pin WSON With Exposed Thermal Pad (Top View)

表 5-2. Pin Functions: DRV Package

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	OUT	Output	Regulated output pin. A 2.2-µF or greater capacitance is required from OUT to ground for stability. For best transient response, use an 8-µF (nominal) or larger ceramic capacitor from OUT to ground. Place the output capacitor as close to OUT as possible.
2	SENSE	Input	SENSE input. This pin is a feedback input to the regulator for SENSE connections. Connecting SENSE to the load helps eliminate voltage errors resulting from trace resistance between OUT and the load.
3	EN	Input	Enable pin. Driving this pin to logic high enables the LDO. Driving this pin to logic low disables the LDO. If enable functionality is not required, EN must be connected to IN or BIAS.
4	BIAS	Input	BIAS pin. This pin enables operation in LILO conditions. For best performance, use 0.47-µF or larger ceramic capacitor from BIAS to ground. Place the bias capacitor as close to BIAS as possible.
5	GND	—	Ground pin. This pin must be connected to ground.
6	IN	Input	Input pin. A 0.75-µF or greater capacitance is required from IN to ground for stability. Place the input capacitor as close to IN as possible.
Thermal Pad		—	The thermal pad is electrically connected to the GND node. Connect to the GND plane for improved thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted.(1)

		MIN	MAX	UNIT
Voltage	Input, V_{IN}	–0.3	2.4	V
	Enable, V_{EN}	–0.3	6.0	
	Bias, V_{BIAS}	–0.3	6.0	
	Sense, V_{SENSE}	–0.3	V_{IN} + 0.3 (2)	
	Output, V_{OUT}	–0.3	V_{IN} + 0.3 (2)	
Current	Maximum output	Internally limited		A
Temperature	Operating junction, T_J	–40	150	°C
	Storage, T_{stg}	–65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The absolute maximum rating is 2.4 V or (V_{IN} + 0.3 V), whichever is less.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±3000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted).(1)

		MIN	NOM	MAX	UNIT
V_{IN}	Input voltage	0.7		2.2	V
V_{BIAS}	Bias voltage	Greater of 2.2 or $V_{OUT(NOM)}$ + 1.4		5.5	V
V_{OUT}	Output voltage	0.5		2.0	V
I_{OUT}	Peak output current	0		1	A
C_{IN}	Input capacitance (2)	0.75			µF
C_{BIAS}	Bias capacitance (4)		0.1		µF
C_{OUT}	Output capacitance, DRV package	2.2		22	µF
C_{OUT}	Output capacitance, YBK package	2.2		47	µF
ESR	Output capacitor series resistance			100	mΩ
T_J	Operating junction temperature	–40		125	℃

(1) All voltages are with respect to GND.
(2) An input capacitor is required to counteract the effect of source resistance and inductance, which may in some cases cause symptoms of system level instability such as ringing or oscillation, especially in the presence of load transients. A larger input capacitor may be necessary depending on the source impedance and system requirements.
(3) A BIAS input capacitor is not required for LDO stability. However, a capacitor with a derated value of at least 0.1 µF is recommended to maintain transient, PSRR, and noise performance.

6.4 Thermal Information

THERMAL METRIC[1]		TPS7A14		UNIT
		WSON	DSBGA	
		6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	72.7	136.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	84.9	1.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	32.7	38.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	3.2	0.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	32.6	38.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	16.8	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

specified at T_J = –40°C to +125°C, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = greater of 2.2 V or $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.1 µF (unless otherwise noted); all typical values are at T_J = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OUT}	Accuracy over temperature	$V_{OUT(NOM)}$ + 0.1 V ≤ V_{IN} ≤ 2.2 V, Greater of 2.2 V or $V_{OUT(NOM)}$ + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, 1 mA ≤ I_{OUT} ≤ 1 A	T_J = –40°C to +125°C, DRV package	–1.25		1	%
			T_J = –40°C to +125°C, YBK package	–1.5		1	
			T_J = –40°C to +85°C	–1		1	
ΔV_{OUT} / ΔV_{IN}	V_{IN} line regulation	$V_{OUT(NOM)}$ + 0.1 V ≤ V_{IN} ≤ 2.2 V, DRV package		–3		3	mV
		$V_{OUT(NOM)}$ + 0.1 V ≤ V_{IN} ≤ 2.2 V, T_J = –40°C to +85°C, YBK package		–2.5		2.5	
ΔV_{OUT} / ΔV_{BIAS}	V_{BIAS} line regulation	$V_{OUT(NOM)}$ + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, DRV package		–3	±0.15	3	mV
		$V_{OUT(NOM)}$ + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, T_J = –40°C to +85°C, YBK package		–2.5	±0.15	2.5	
ΔV_{OUT} / ΔI_{OUT}	Load regulation	1 mA ≤ I_{OUT} ≤ 1 A			0.2		%/A
$I_{Q(BIAS)}$	Bias pin current	I_{OUT} = 0 mA, DRV package				43	µA
		I_{OUT} = 0 mA, T_J = –40°C to +85°C, YBK package				26	
		I_{OUT} = 1 A, DRV package				17	mA
		I_{OUT} = 1 A, T_J = –40°C to +85°C, YBK package				12	
$I_{Q(IN)}$	Input pin current[1]	I_{OUT} = 0 mA, DRV package				118	µA
		I_{OUT} = 0 mA, TJ = –40°C to +85°C				5.7	
I_{GND}	Ground pin current	I_{OUT} = 1 A, DRV package			480	660	µA
		I_{OUT} = 1 A, T_J = –40°C to +85°C			480	620	
$I_{SHDN(BIAS)}$	V_{BIAS} shutdown current	V_{IN} = 2.2 V, V_{BIAS} = 5.5 V, V_{EN} ≤ 0.2 V, DRV package			0.3	9	µA
		V_{IN} = 2.2 V, V_{BIAS} = 5.5 V, V_{EN} ≤ 0.2 V, T_J = –40°C to +85°C			0.3	3.8	
$I_{SHDN(IN)}$	V_{IN} shutdown current	V_{IN} = 1.8 V, V_{BIAS} = 5.5 V, V_{EN} ≤ 0.2 V, DRV package			1	41	µA
		V_{IN} = 1.8 V, V_{BIAS} = 5.5 V, V_{EN} ≤ 0.2 V, T_J = –40°C to +85°C			1	9.2	
I_{CL}	Output current limit	V_{OUT} = 0.95 × $V_{OUT(NOM)}$		1.035	1.6	2.45	A
I_{SC}	Short circuit current limit	V_{OUT} = 0 V			600		mA
$V_{DO(IN)}$	V_{IN} dropout voltage[2]	V_{IN} = 0.95 x $V_{OUT(NOM)}$, I_{OUT} = 1 A	T_J = –40°C to + 125°C			99	mV
			T_J = –40°C to + 85°C, DRV package			77	
			T_J = –40°C to + 85°C, YBK package			70	

6.5 Electrical Characteristics (continued)

specified at T_J = –40°C to +125°C, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = greater of 2.2 V or $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.1 µF (unless otherwise noted); all typical values are at T_J = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{DO(BIAS)}$	V_{BIAS} dropout voltage(2)	V_{BIAS} = greater of 1.7V or $V_{OUT(nom)}$ + 0.6 V, V_{SENSE} = 0.95 x $V_{OUT(nom)}$, I_{OUT} = 1 A, DRV package				1.115	V
		V_{BIAS} = greater of 1.7V or $V_{OUT(nom)}$ + 0.6 V, V_{SENSE} = 0.95 x $V_{OUT(nom)}$, I_{OUT} = 1 A, YBK package				1.1	
V_{IN} PSRR	V_{IN} power-supply rejection ratio	f = 100 Hz	I_{OUT} = 3 mA		90		dB
			I_{OUT} = 500 mA		80		
			I_{OUT} = 1 A		80		
		f = 1 kHz	I_{OUT} = 3 mA		90		
			I_{OUT} = 500 mA		80		
			I_{OUT} = 1 A		70		
		f = 10 kHz	I_{OUT} = 3 mA		70		
			I_{OUT} = 500 mA		60		
			I_{OUT} = 1 A		50		
		f = 100 kHz	I_{OUT} = 3 mA		60		
			I_{OUT} = 500 mA		43		
			I_{OUT} = 1 A		33		
		f = 1 MHz	I_{OUT} = 3 mA		60		
			I_{OUT} = 500 mA		24		
			I_{OUT} = 1 A		15		
		f = 1 MHz, V_{IN} = V_{OUT} + 150 mV	I_{OUT} = 3 mA		69		
			I_{OUT} = 500 mA		42		
			I_{OUT} = 1 A		33		
V_{BIAS} PSRR	V_{BIAS} power-supply rejection ratio	f = 1 kHz	I_{OUT} = 500 mA		65		dB
		f = 100 kHz			45		
		f = 1 MHz			25		
V_n	Output voltage noise	Bandwidth = 10 Hz to 100 kHz, V_{OUT} = 0.8 V, 5mA ≤ I_{OUT} ≤ 1 A			7.2		μV_{RMS}
$V_{UVLO(BIAS)}$	Bias supply UVLO	V_{BIAS} rising		1.15	1.42	1.7	V
		V_{BIAS} falling		1.0	1.3	1.63	
$V_{UVLO\_HYST(BIAS)}$	Bias supply hysteresis	V_{BIAS} hysteresis			100		mV
$V_{UVLO(IN)}$	Input supply UVLO	V_{IN} rising		584	603	623	mV
		V_{IN} falling		530	552	566	
$V_{UVLO\_HYST(IN)}$	Input supply hysteresis	V_{IN} hysteresis			50		mV
t_{STR}	Start-up time(3)				186		µs
$V_{EN(HI)}$	EN pin logic high voltage(4)			0.6		6	V
$V_{EN(LOW)}$	EN pin logic low voltage(4)			0		0.25	V
I_{EN}	EN pin current	EN = 5.5 V, DRV package		-25	10	25	nA
		EN = 5.5 V, T_J = –40°C to +85°C		-20	10	20	
$R_{PULLDOWN}$	Pulldown resistor	V_{IN} = 0.9 V, $V_{OUT(nom)}$ = 0.8 V, V_{BIAS} = 1 V, V_{EN} = 0 V, P version only			36		Ω
T_{SD}	Thermal shutdown temperature	Shutdown, temperature rising			165		°C
		Reset, temperature falling			140		

(1) This is the current flowing from V_{IN} to GND.
(2) Dropout is not measured for V_{OUT} < 0.6 V. V_{BIAS} dropout applies only for V_{BIAS} of 2.2 V or greater.
(3) Startup time = time from EN assertion to 0.95 × $V_{OUT(NOM)}$.
(4) An input voltage within the minimum to maximum range is interpreted as the correct logic level.

6.6 Switching Characteristics

specified at T_J = –40°C to +125°C, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = greater of 2.2 V or $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = 1.0 V, C_{IN} = 1 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.1 µF (unless otherwise noted); all typical values are at T_J = 25°C; all transients values are over multiple load or line pulses with periods of 100µs on (high load) and 100µs off (low load)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ΔV_{OUT}	Line transient(1)	V_{IN} = ($V_{OUT(NOM)}$ + 0.1 V) to 2.1 V	Transition time, t_R = 1 V / µs			1	% V_{OUT}
		V_{IN} = 2.1 V to ($V_{OUT(NOM)}$) + 0.1 V)	Transition time, t_F = 1 V / µs	–1			
ΔV_{OUT}	Load transient(1)	I_{OUT} = 3 mA to 600 mA	Transition time, t_R = 20 µs, t_F = 20 µs, t_{OFF} = 200 µs, t_{ON} = 1 ms, C_{IN} = 5 µF, C_{OUT} = 5 µF	–2			% V_{OUT}
		I_{OUT} = 600 mA to 3 mA				2	

(1) This specification is verified by design.

6.7 Typical Characteristics

at operating temperature T_J = 25°C, $V_{OUT(NOM)}$ = 0.8 V, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF (unless otherwise noted)

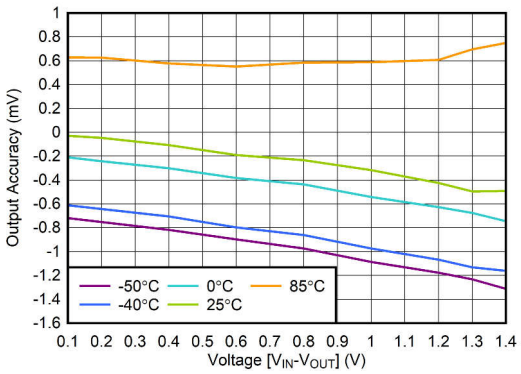


図 6-1. Output Voltage Accuracy vs V_{IN}

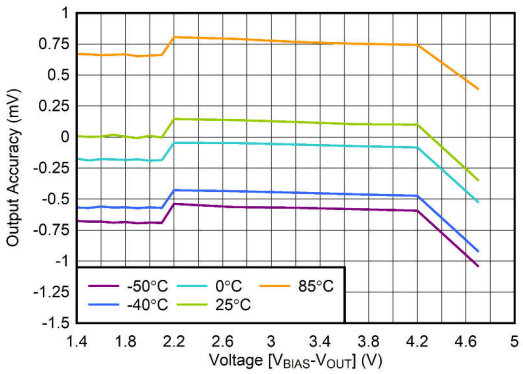


図 6-2. Output Voltage Accuracy vs V_{BIAS}

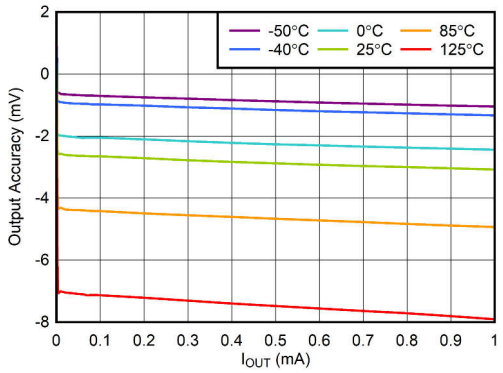


図 6-3. Output Voltage Accuracy vs I_{OUT}

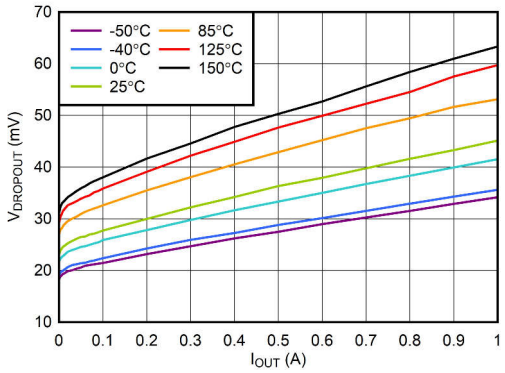


図 6-4. V_{IN} Dropout Voltage vs I_{OUT}

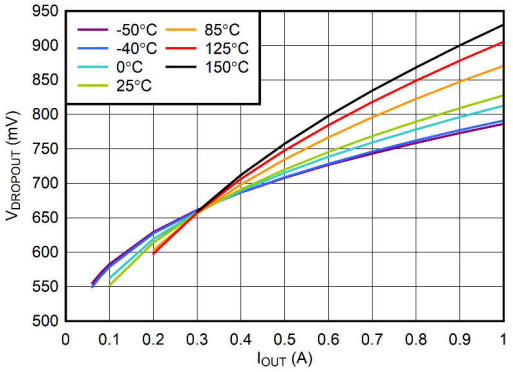


図 6-5. V_{BIAS} Dropout Voltage vs I_{OUT}

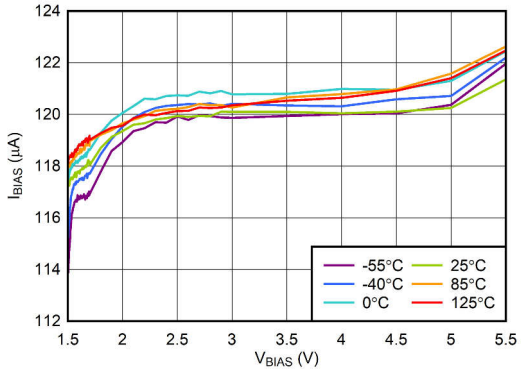
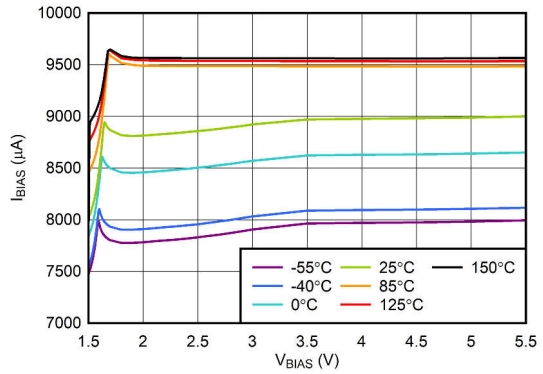


図 6-6. V_{BIAS} Input Current vs V_{BIAS}

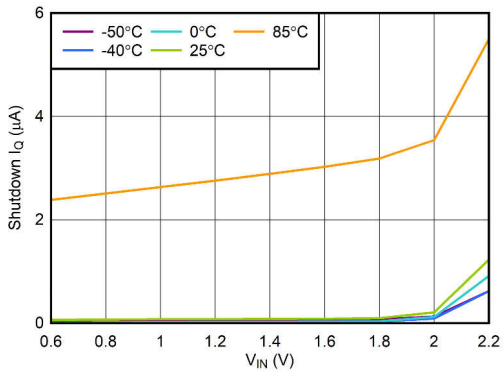
6.7 Typical Characteristics (continued)

at operating temperature T_J = 25°C, $V_{OUT(NOM)}$ = 0.8 V, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF (unless otherwise noted)



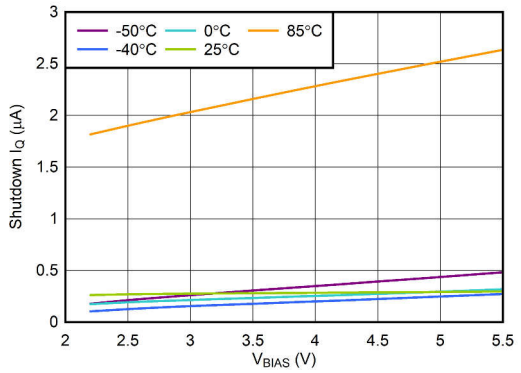
I_{OUT} = 1 A

図 6-7. V_{BIAS} Input Current vs V_{BIAS}



I_{OUT} = 0 mA

図 6-8. V_{IN} Shutdown I_Q vs V_{IN}



I_{OUT} = 0 A, V_{IN} = 1 V

図 6-9. V_{BIAS} Shutdown I_Q vs V_{BIAS}

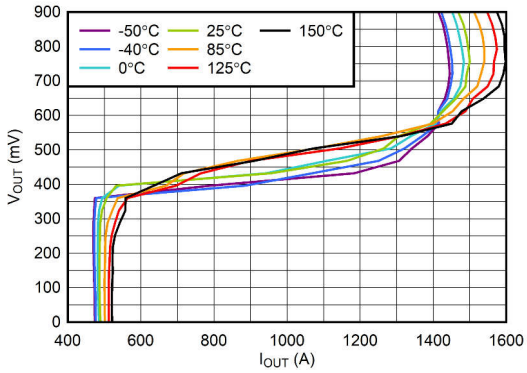


図 6-10. V_{OUT} Foldback Current Limit vs Output Current

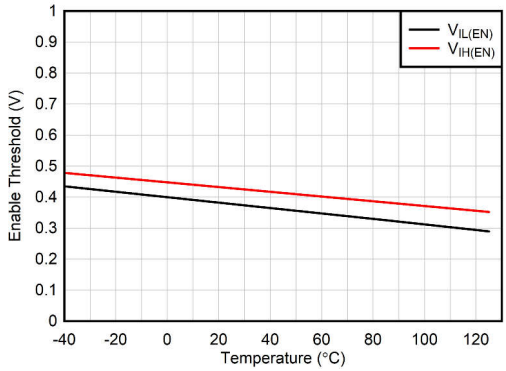


図 6-11. Enable Threshold vs Temperature

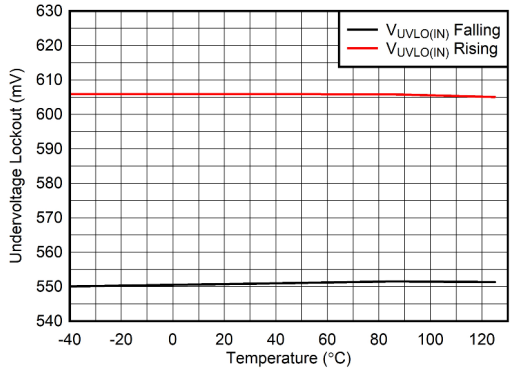


図 6-12. V_{IN} UVLO vs Temperature

6.7 Typical Characteristics (continued)

at operating temperature T_J = 25°C, $V_{OUT(NOM)}$ = 0.8 V, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF (unless otherwise noted)

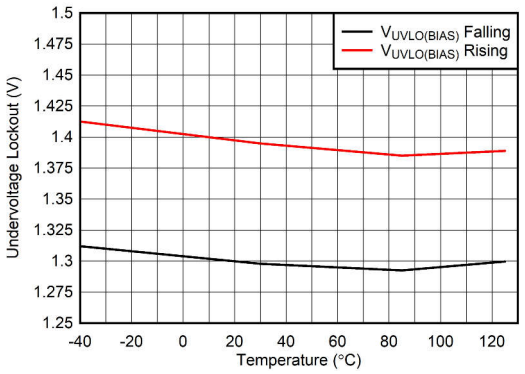
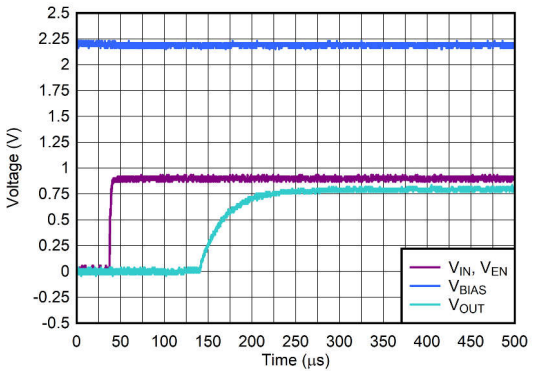
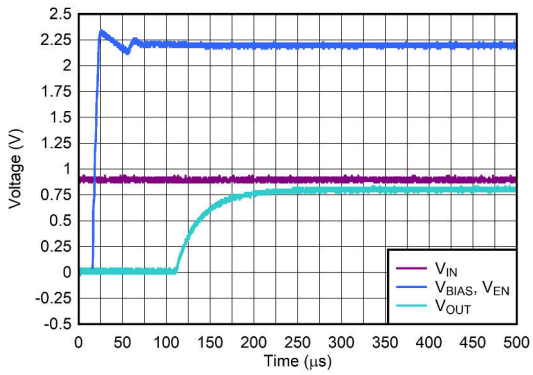


図 6-13. V_{BIAS} UVLO vs Temperature



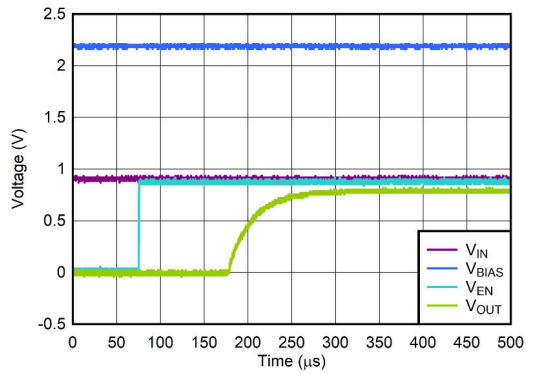
t_r = 1 µs

図 6-14. Start-Up With V_{BIAS} Before V_{IN}



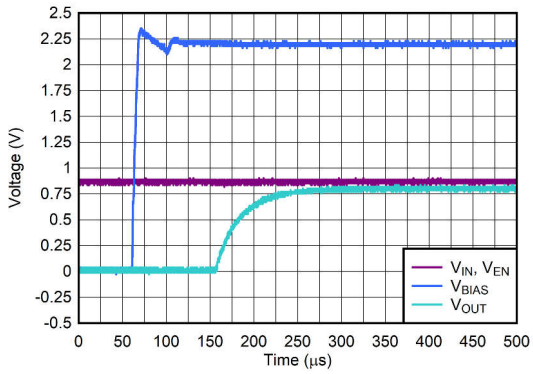
t_r = 1 µs

図 6-15. Start-Up With V_{IN} Before V_{BIAS} and V_{EN}



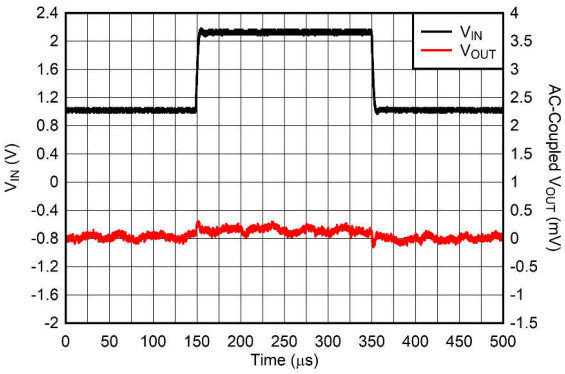
t_r = 1 µs

図 6-16. Start-Up With V_{IN} and V_{BIAS} Before V_{EN}



t_r = 1 µs

図 6-17. Start-Up With V_{IN} and V_{EN} Before V_{BIAS}

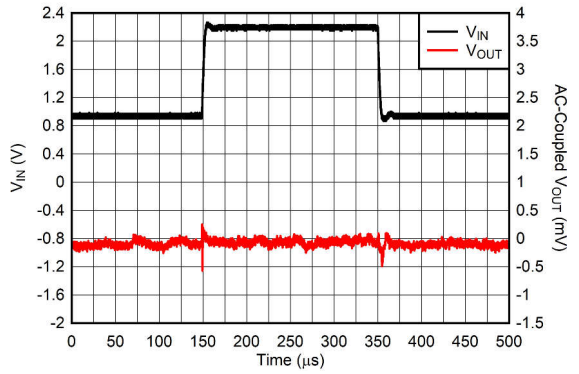


t_r = t_f = 10 µs, I_{OUT} = 1 mA

図 6-18. Line Transient From 1 V to 2.2 V

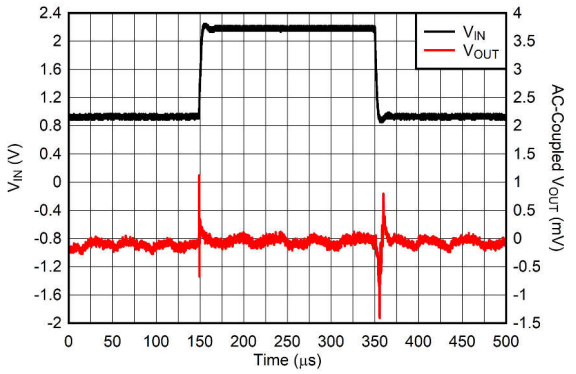
6.7 Typical Characteristics (continued)

at operating temperature T_J = 25°C, $V_{OUT(NOM)}$ = 0.8 V, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF (unless otherwise noted)



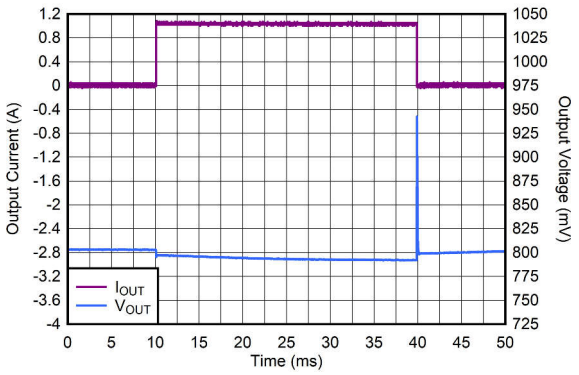
t_r = t_f = 10 µs, I_{OUT} = 500 mA

図 6-19. Line Transient From 1 V to 2.2 V



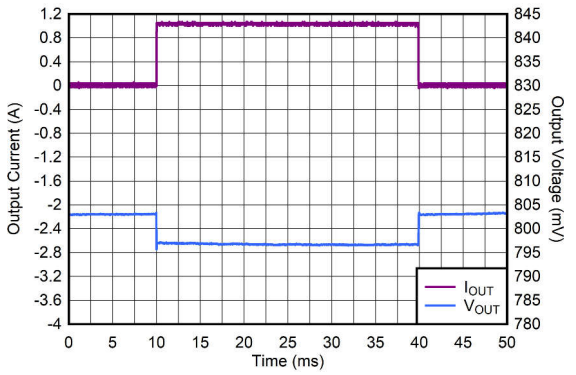
t_r = t_f = 10 µs, I_{OUT} = 1 A

図 6-20. Line Transient From 1 V to 2.2 V



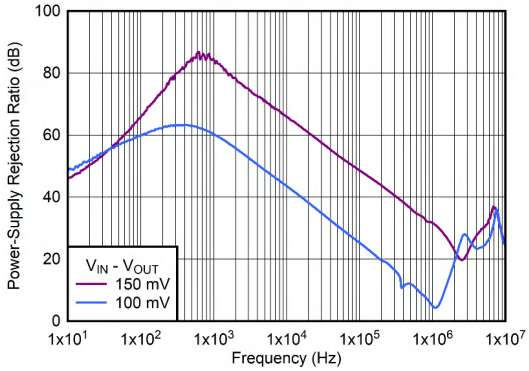
t_r = t_f = 1 µs

図 6-21. Load Transient From 100 µA to 1 A



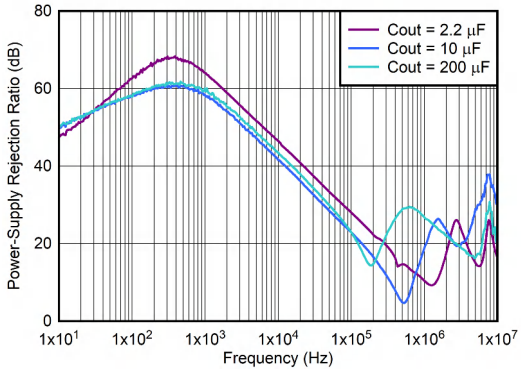
t_r = t_f = 20 µs

図 6-22. Load Transient From 100 µA to 1 A



C_{BIAS} = 0 µF, I_{OUT} = 1 A

図 6-23. PSRR vs Frequency and V_{IN} – V_{OUT}

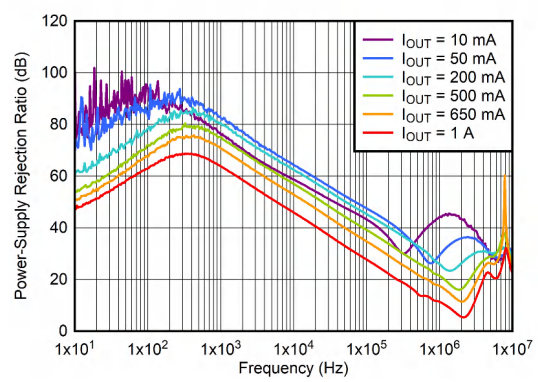


C_{BIAS} = 0 µF, I_{OUT} = 1 A

図 6-24. PSRR vs Frequency and C_{OUT}

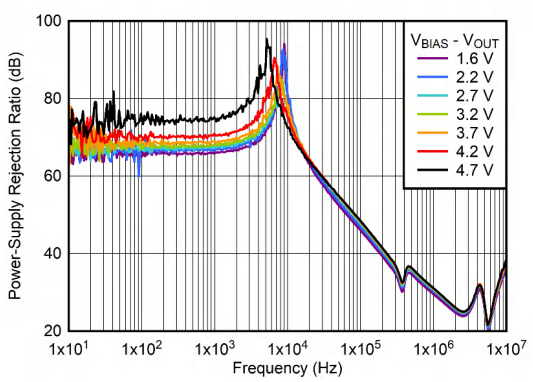
6.7 Typical Characteristics (continued)

at operating temperature T_J = 25°C, $V_{OUT(NOM)}$ = 0.8 V, V_{IN} = $V_{OUT(NOM)}$ + 0.1 V, V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, I_{OUT} = 1 mA, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF (unless otherwise noted)



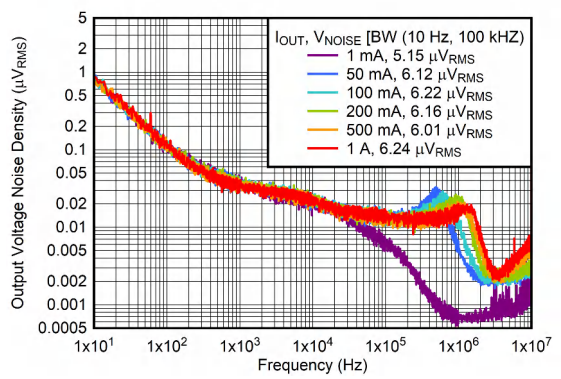
C_{BIAS} = 0 µF

図 6-25. PSRR vs Frequency and I_{OUT}



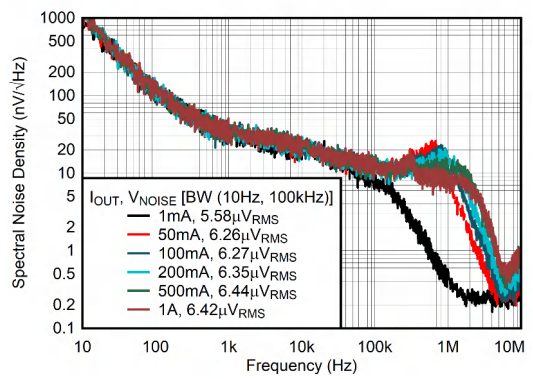
C_{BIAS} = 0 µF

図 6-26. PSRR vs Frequency and V_{BIAS} – V_{OUT}



YCK package, V_{OUT} = 0.8 V

図 6-27. Output Noise vs Frequency and I_{OUT}



DRV package, V_{OUT} = 1.8 V, $_{BIAS}$ = 5 V

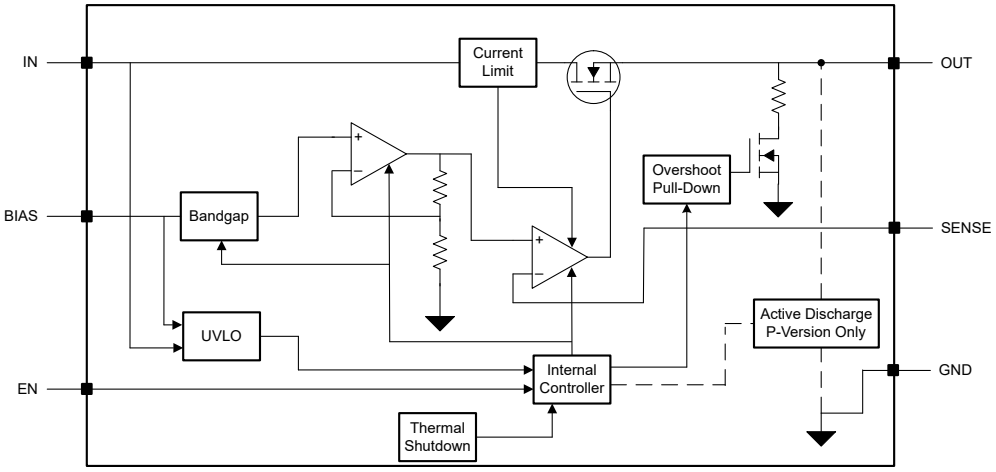
図 6-28. Output Noise vs Frequency and I_{OUT}

7 Detailed Description

7.1 Overview

The TPS7A14 is a low-input, ultra-low dropout, low-quiescent-current linear regulator that is optimized for excellent transient performance. These characteristics make the device designed for most battery-powered applications. The low operating V_{IN} – V_{OUT}, combined with the BIAS pin, dramatically improve the efficiency of low-voltage output applications by powering the voltage reference and control circuitry and allowing the use of a pre-regulated, low-voltage input supply (IN) for the main power path. This low-dropout regulator (LDO) offers foldback current limit, shutdown, thermal protection, and an optional active discharge.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Excellent Transient Response

The TPS7A14 responds quickly to a change on the input supply (line transient) or the output current (load transient) given the device high input impedance and low output impedance across frequency. This same capability also means that this LDO has a high power-supply rejection ratio (PSRR) and, when coupled with a low internal noise floor (e_n), the LDO can be used to create an excellent power supply with outstanding line and load transient performance.

The choice of external component values optimizes the transient response; see the *Input, Output, and Bias Capacitor Requirements* section for proper capacitor selection.

7.3.2 Global Undervoltage Lockout (UVLO)

The TPS7A14 uses two undervoltage lockout circuits: one on the BIAS pin and one on the IN pin to prevent the device from turning on before both V_{BIAS} and V_{IN} rise above their lockout voltages. The two UVLO signals are connected internally through an AND gate, as shown in 図 7-1, that turns off the device when the voltage on either input is below their respective UVLO thresholds.

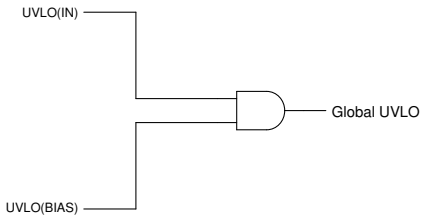


図 7-1. Global UVLO circuit

7.3.3 Enable Input

The enable input (EN) is active high. Applying a voltage greater than $V_{EN(HI)}$ to EN enables the regulator output voltage, and applying a voltage less than $V_{EN(LOW)}$ to EN disables the regulator output. If independent control of the output voltage is not needed, connect EN to either IN or BIAS.

7.3.4 Internal Foldback Current Limit

The device has an internal current limit circuit that protects the regulator during transient high-load current faults or shorting events. The current limit is a hybrid brick-wall foldback scheme. The current limit transitions from a brick-wall scheme to a foldback scheme at the foldback voltage ($V_{FOLDBACK}$). In a high-load current fault with the output voltage above $V_{FOLDBACK}$, the brick-wall scheme limits the output current to the current limit (I_{CL}). When the voltage drops below $V_{FOLDBACK}$, a foldback current limit activates that scales back the current as the output voltage approaches GND. When the output is shorted, the device supplies a typical current called the short-circuit current limit (I_{SC}). I_{CL} and I_{SC} are listed in the *Electrical Characteristics* table.

For this device, $V_{FOLDBACK}$ is approximately 60% × $V_{OUT(nom)}$.

The output voltage is not regulated when the device is in current limit. When a current limit event occurs, the device begins to heat up because of the increase in power dissipation. When the device is in brick-wall current limit, the pass transistor dissipates power [(V_{IN} – V_{OUT}) × I_{CL}]. When the device output is shorted and the output is below $V_{FOLDBACK}$, the pass transistor dissipates power [(V_{IN} – V_{OUT}) × I_{SC}]. If thermal shutdown is triggered, the device turns off. After the device cools down, the internal thermal shutdown circuit turns the device back on. If the output current fault condition continues, the device cycles between current limit and thermal shutdown. For more information on current limits, see the *Know Your Limits* application report.

図 7-2 shows a diagram of the foldback current limit.

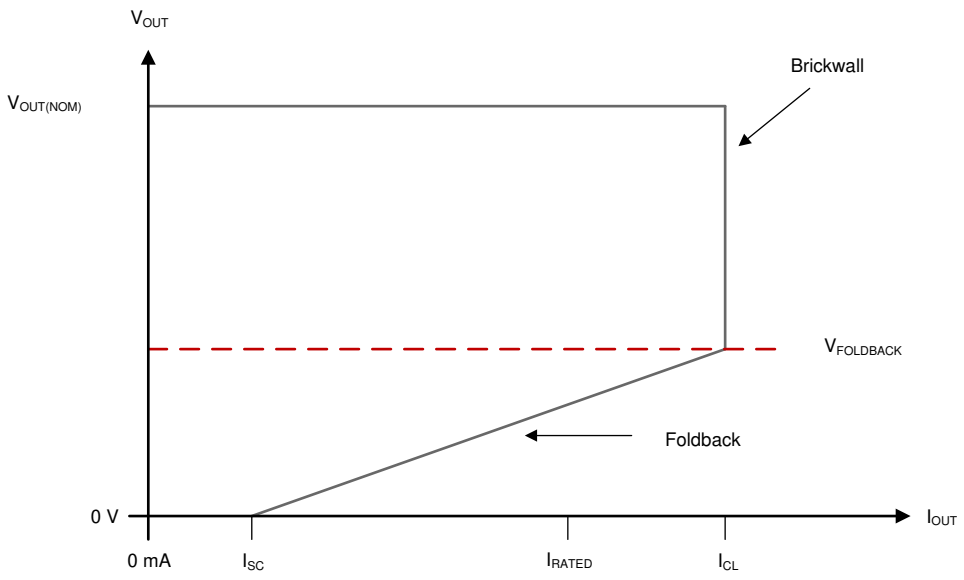


図 7-2. Foldback Current Limit

7.3.5 Active Discharge

The active discharge function uses an internal MOSFET that connects a resistor ($R_{PULLDOWN}$) to ground when the LDO is disabled in order to actively discharge the output voltage. The active discharge circuit is activated by driving EN to logic low to disable the device, when the voltage at IN or BIAS is below the UVLO threshold, or when the regulator is in thermal shutdown.

The discharge time after disabling the device depends on the output capacitance (C_{OUT}) and the load resistance (R_L) in parallel with the pulldown resistor.

Do not rely on the active discharge circuit for discharging a large amount of output capacitance after the input supply has collapsed because reverse current can flow from the output to the input. This reverse current flow can cause damage to the device. Limit reverse current to no more than 5% of the rated output current for a short period of time.

7.3.6 Thermal Shutdown

The internal thermal shutdown protection circuit disables the output when the thermal junction temperature (T_J) of the pass transistor rises to the thermal shutdown temperature threshold, $T_{SD(shutdown)}$ (typical). The thermal shutdown circuit hysteresis makes sure that the LDO resets (turns on) when the temperature falls to $T_{SD(reset)}$ (typical).

The thermal time constant of the semiconductor die is fairly short; thus, the device can cycle on and off when thermal shutdown is reached until the power dissipation is reduced. Power dissipation during start up can be high from large $V_{IN} – V_{OUT}$ voltage drops across the device or from high inrush currents charging large output capacitors. Under some conditions, the thermal shutdown protection disables the device before start up completes.

For reliable operation, limit the junction temperature to the maximum listed in the *Recommended Operating Conditions* table. Operation above this maximum temperature causes the device to exceed operational specifications. Although the internal protection circuitry is designed to protect against thermal overload

conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the regulator into thermal shutdown or above the maximum recommended junction temperature reduces long-term reliability.

7.4 Device Functional Modes

表 7-1 shows the conditions that lead to the different modes of operation. See the *Electrical Characteristics* table for parameter values.

表 7-1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER				
	V_{IN}	V_{BIAS}	V_{EN}	I_{OUT}	T_J
Normal mode	$V_{IN} \geq V_{OUT\ (nom)} + V_{DO}$ and $V_{IN} \geq V_{IN(min)}$	$V_{BIAS} \geq V_{OUT} + V_{DO(BIAS)}$	$V_{EN} \geq V_{IH(EN)}$	$I_{OUT} < I_{CL}$	$T_J < T_{SD}$ for shutdown
Dropout mode	$V_{IN(min)} < V_{IN} < V_{OUT\ (nom)} + V_{DO(IN)}$	$V_{BIAS} < V_{OUT} + V_{DO(BIAS)}$	$V_{EN} > V_{IH(EN)}$	$I_{OUT} < I_{CL}$	$T_J < T_{SD}$ for shutdown
Disabled mode (any true condition disables the device)	$V_{IN} < V_{UVLO(IN)}$	$V_{BIAS} < V_{BIAS(UVLO)}$	$V_{EN} < V_{IL(EN)}$	—	$T_J \geq T_{SD}$ for shutdown

7.4.1 Normal Operation

The device regulates to the nominal output voltage when the following conditions are met:

- The input voltage is greater than the nominal output voltage plus the dropout voltage ($V_{OUT(nom)} + V_{DO}$)
- The bias voltage is greater than the nominal output voltage plus the dropout voltage ($V_{OUT(nom)} + V_{DO}$)
- The output current is less than the current limit ($I_{OUT} < I_{CL}$)
- The device junction temperature is less than the thermal shutdown temperature ($T_J < T_{SD(shutdown)}$)
- The enable voltage has previously exceeded the enable rising threshold voltage and has not yet decreased to less than the enable falling threshold

7.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. Similarly, if the bias voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode as well. In this mode, the output voltage tracks the input voltage. During this mode, the transient performance of the device becomes significantly degraded because the pass transistor is in the ohmic or triode region, and acts as a switch. Line or load transients in dropout can result in large output voltage deviations.

When the device is in a steady dropout state, defined as when the device is in dropout, ($V_{IN} < V_{OUT} + V_{DO}$ or $V_{BIAS} < V_{OUT} + V_{DO}$ directly after being in normal regulation state, but not during start up), the pass transistor is driven into the ohmic or triode region. When the input voltage returns to a value greater than or equal to the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$), the output voltage can overshoot for a short time when the device pulls the pass transistor back into the linear region.

7.4.3 Disable Mode

The output of the device can be shutdown by forcing the voltage of the enable pin to less than $V_{IL(EN)}$ (see the *Electrical Characteristics* table). When disabled, the pass transistor is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground by an internal discharge circuit from the output to ground.

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

Successfully implementing an LDO in a system depends on the system requirements. This section discusses key device features and how to best implement them to achieve a reliable design.

8.1.1 Recommended Capacitor Types

The regulator is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input, output, and bias pins. Multilayer ceramic capacitors are the industry standard for use with LDOs, but must be used with good judgment. Ceramic capacitors that use X7R-, X5R-, and COG-rated dielectric materials provide relatively good capacitive stability across temperature, whereas the use of Y5V-rated capacitors is discouraged because of large variations in capacitance. Regardless of the ceramic capacitor type selected, ceramic capacitance varies with operating voltage and temperature. Generally, assume that effective capacitance decreases by as much as 50%. The input, output, and bias capacitors recommended in the *Recommended Operating Conditions* table account for an effective capacitance of approximately 50% of the nominal value.

8.1.2 Input, Output, and Bias Capacitor Requirements

A minimum input ceramic capacitor is required for stability. A minimum output ceramic capacitor is also required for stability, see the *Recommended Operating Conditions* table for the minimum capacitors values.

The input capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. A higher-value input capacitor can be necessary if large, fast rise-time load or line transients are anticipated, or if the device is located several inches from the input power source. Dynamic performance of the device is improved with the use of an output capacitor larger than the minimum value specified in the *Recommended Operating Conditions* table.

Although a bias capacitor is not required, good design practice is to connect a 0.1-µF ceramic capacitor from BIAS to GND. This capacitor counteracts reactive bias source if the source impedance is not sufficiently low. Place the input, output, and bias capacitors as close as possible to the device to minimize trace parasitics.

If the BIAS source is susceptible to fast voltage drops (for example, a 2-V drop in less than 1 µs) when the LDO load current is near the maximum value, the BIAS voltage drop can cause the output voltage to fall briefly. In such cases, use a BIAS capacitor large enough to slow the voltage ramp rate to less than 0.5 V/µs. For smaller or slower BIAS transients, any output voltage dips must be less than 5% of the nominal voltage.

8.1.3 Dropout Voltage

Dropout voltage (V_{DO}) is defined as the input voltage minus the output voltage ($V_{IN} – V_{OUT}$) at the rated output current (I_{RATED}), where the pass transistor is fully on. I_{RATED} is the maximum I_{OUT} listed in the *Recommended Operating Conditions* table. The pass transistor is in the ohmic or triode region of operation, and acts as a switch. The dropout voltage indirectly specifies a minimum input voltage greater than the nominal programmed output voltage at which the output voltage is expected to stay in regulation. If the input voltage falls to less than the nominal output regulation, then the output voltage falls as well.

For a CMOS regulator, the dropout voltage is determined by the drain-source on-state resistance ($R_{DS(ON)}$) of the pass transistor. Therefore, if the linear regulator operates at less than the rated current, the dropout voltage for that current scales accordingly. Use 式 1 to calculate the $R_{DS(ON)}$ of the device.

$$R_{DS(ON)} = \frac{V_{DO}}{I_{RATED}} \quad (1)$$

The use of bias rail enables the TPS7A14 to achieve a lower dropout voltage between IN and OUT. However, a minimum bias voltage above the nominal programmed output voltage must be maintained. 図 6-13 specifies the minimum V_{BIAS} headroom required to maintain output regulation.

8.1.4 Behavior During Transition From Dropout Into Regulation

Some applications can have transients that place this device into dropout, especially when this device can be powered from a battery with relatively high ESR. The load transient saturates the output stage of the error amplifier when the pass transistor is driven fully on, making the pass transistor function like a resistor from V_{IN} to V_{OUT}. The error amplifier response time to this load transient is extended because the error amplifier must first recover from saturation and then must place the pass transistor back into active mode. During this recovery period, V_{OUT} overshoots because the pass transistor is functioning as a resistor from V_{IN} to V_{OUT}.

When V_{IN} ramps up slowly for start up, the slow ramp-up voltage can place the device in dropout. As with many other LDOs, the output can overshoot on recovery from this condition. However, this condition is easily avoided through the use of the enable signal.

If operating under these conditions, apply a higher dc load current or increase the output capacitance to reduce the overshoot. These approaches provide a path to absorb the excess charge.

8.1.5 Device Enable Sequencing Requirement

The IN, BIAS, and EN pin voltages can be sequenced in any order without causing damage to the device. Start up is always monotonic regardless of the sequencing order or the ramp rates of the IN, BIAS, and EN pins. See the *Recommended Operating Conditions* table for proper voltage ranges of the IN, BIAS, and EN pins.

8.1.6 Load Transient Response

The load-step transient response is the output voltage response by the LDO to a step in load current while output voltage regulation is maintained. See 図 6-21 and 図 6-22 for typical load transient response plots. There are two key transitions during a load transient response: the transition from a light to a heavy load, and the transition from a heavy to a light load. The regions in 図 8-1 are broken down as described in this section. Regions A, E, and H are where the output voltage is in steady-state operation.

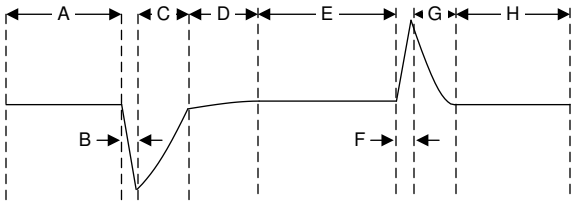


図 8-1. Load Transient Waveform

During transitions from a light load to a heavy load, the following behavior can be observed:

- The initial voltage dip is a result of the depletion of the output capacitor charge and parasitic impedance to the output capacitor (region B)
- Recovery from the dip results from the LDO increasing the sourcing current, and leads to output voltage regulation (region C)

During transitions from a heavy load to a light load, the following behavior can be observed:

- The initial voltage rise results from the LDO sourcing a large current, and leads to an increase in the output capacitor charge (region F)
- Recovery from the rise results from the LDO decreasing the sourcing current in combination with the load discharging the output capacitor (region G)

A larger output capacitance reduces the peaks during a load transient but slows down the response time of the device. A larger dc load also reduces the peaks because the amplitude of the transition is lowered and a higher current discharge path is provided for the output capacitor.

8.1.7 Undervoltage Lockout Circuit Operation

The V_{IN} UVLO circuit makes sure that the regulator remains disabled when the input supply voltage is below the minimum operational voltage range, and makes sure that the regulator shuts down when the input supply collapses. Similarly, the V_{BIAS} UVLO circuit makes sure that the regulator remains disabled when the bias supply voltage is less than the minimum operational voltage range, and makes sure that the regulator shuts down when the bias supply collapses.

図 8-2 shows the UVLO circuit response to various input or bias voltage events. The diagram can be separated into the following parts:

- Region A: The output remains off while the input or bias voltage is below the UVLO rising threshold
- Region B: Normal operation, regulating device
- Region C: Brownout event above the UVLO falling threshold (UVLO rising threshold – UVLO hysteresis). The output can possibly fall out of regulation but the device remains enabled.
- Region D: Normal operation, regulating device
- Region E: Brownout event below the UVLO falling threshold. The device is disabled in most cases and the output falls as a result of the load and active discharge circuit. The device is re-enabled when the UVLO rising threshold is reached and a normal start up follows.
- Region F: Normal operation followed by the input or bias falling to the UVLO falling threshold
- Region G: The device is disabled when the input or bias voltages fall below the UVLO falling threshold to 0 V. The output falls as a result of the load and active discharge circuit.

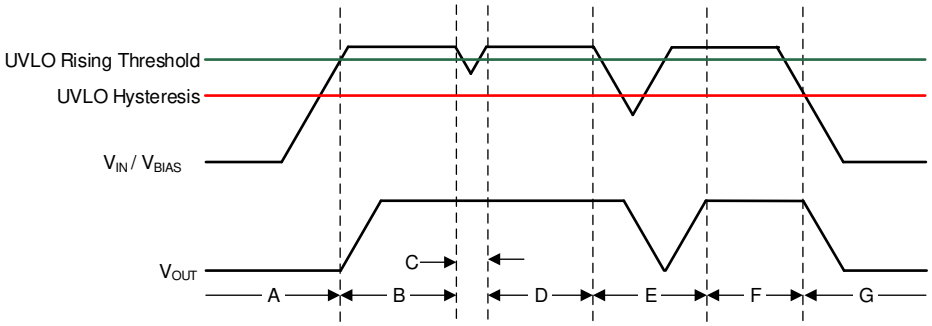


図 8-2. Typical V_{IN} or V_{BIAS} UVLO Circuit Operation

8.1.8 Power Dissipation (P_D)

Circuit reliability demands that proper consideration be given to device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must be as free as possible of other heat-generating devices that cause added thermal stresses.

式 2 calculates the maximum allowable power dissipation for the device in a given package:

$$P_{D\text{-}MAX} = [(T_J - T_A) / R_{\theta JA}] \quad (2)$$

式 3 represents the actual power being dissipated in the device:

$$P_D = ((I_{GND(IN)} + I_{IN}) \times V_{IN} + I_{GND(BIAS)} \times V_{BIAS}) - (I_{OUT} \times V_{OUT}) \quad (3)$$

If the load current is much greater than $I_{GND(IN)}$ and $I_{GND(BIAS)}$ 式 3 can be simplified as:

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (4)$$

Power dissipation can be minimized, and thus greater efficiency achieved, by proper selection of the system voltage rails. Proper selection allows the minimum input-to-output voltage differential to be obtained. The low dropout of the TPS7A14 allows for maximum efficiency across a wide range of output voltages.

The main heat conduction path depends on the ambient temperature and the thermal resistance across the various interfaces between the die junction and ambient air.

The maximum allowable junction temperature (T_J) determines the maximum power dissipation for the device. According to 式 5, maximum power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T_A). The equation is rearranged in 式 6 for output current.

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad (5)$$

$$I_{OUT} = (T_J - T_A) / [R_{\theta JA} \times (V_{IN} - V_{OUT})] \quad (6)$$

Unfortunately, this thermal resistance ($R_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The $R_{\theta JA}$ recorded in the *Electrical Characteristics* table is determined by the JEDEC standard, PCB, and copper-spreading area, and is only used as a relative measure of package thermal performance. For a well-designed thermal layout, $R_{\theta JA}$ is actually the sum of the YBK package junction-to-case (bottom) thermal resistance ($R_{\theta JC(bot)}$) plus the thermal resistance contribution by the PCB copper.

8.1.9 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi (Ψ) thermal metrics to estimate the junction temperatures of the LDO when in-circuit on a typical PCB board application. These metrics are not strictly speaking thermal resistances, but rather offer practical and relative means of estimating junction temperatures. These psi metrics are determined to be significantly independent of the copper-spreading area. The key thermal metrics (Ψ_{JT} and Ψ_{JB}) are used in accordance with 式 7 and are given in the *Electrical Characteristics* table.

$$\Psi_{JT} : T_J = T_T + \Psi_{JT} \times P_D \text{ and } \Psi_{JB} : T_J = T_B + \Psi_{JB} \times P_D \quad (7)$$

where:

- P_D is the power dissipated as explained in 式 3 and the *Power Dissipation (P_D)* section
- T_T is the temperature at the center-top of the device package
- T_B is the PCB surface temperature measured 1 mm from the device package and centered on the package edge

8.1.10 Recommended Area for Continuous Operation

The operational area of an LDO is limited by the dropout voltage, output current, junction temperature, and input voltage. The recommended area for continuous operation for a linear regulator is provided in 図 8-3 and can be separated into the following regions:

- Dropout voltage limits the minimum differential voltage between the input and the output ($V_{IN} - V_{OUT}$) at a given output current level; see the *Dropout Operation* section for more details.
- The rated output current limits the maximum recommended output current level. Exceeding this rating causes the device to fall out of specification.
- The rated junction temperature limits the maximum junction temperature of the device. Exceeding this rating causes the device to fall out of specification and reduces long-term reliability.
  - 式 6 provides the shape of the slope. The slope is nonlinear because the maximum rated junction temperature of the LDO is controlled by the power dissipation across the LDO, thus when $V_{IN} - V_{OUT}$ increases the output current must decrease.
- The rated input voltage range governs both the minimum and maximum of $V_{IN} - V_{OUT}$.

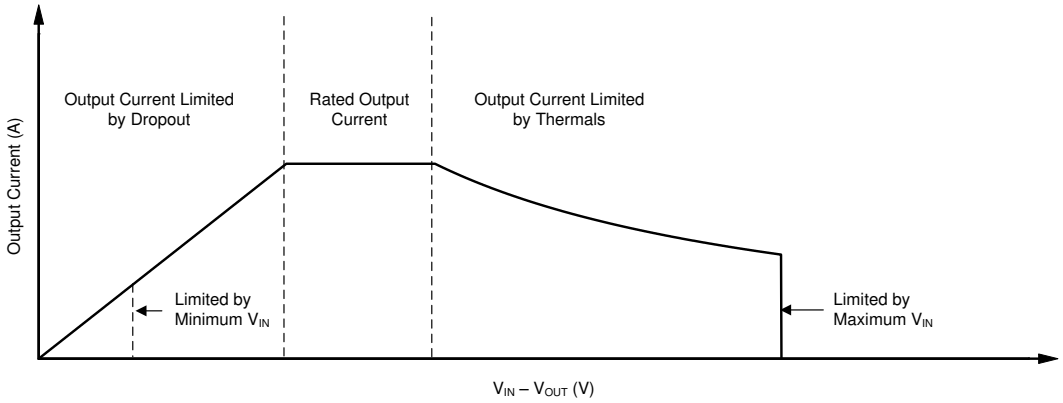


図 8-3. Continuous Operation Diagram With Description of Regions

8.2 Typical Application

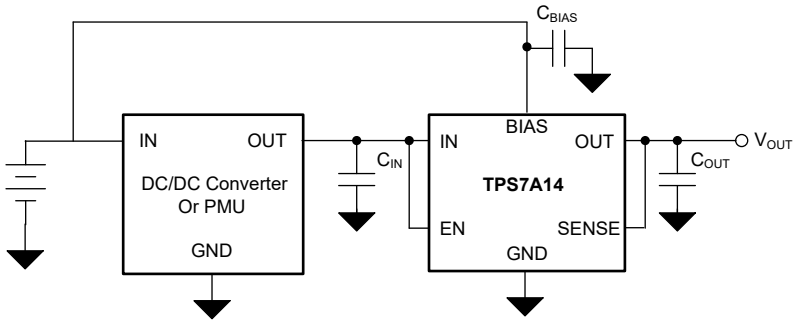


図 8-4. High-Efficiency Supply From a Rechargeable Battery

8.2.1 Design Requirements

表 8-1 lists the parameters for this design example.

表 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{IN}	0.95 V
V_{BIAS}	2.4 V to 5.5 V
V_{OUT}	0.8 V
I_{OUT}	600 mA (typical), 900 mA (peak)

8.2.2 Detailed Design Procedure

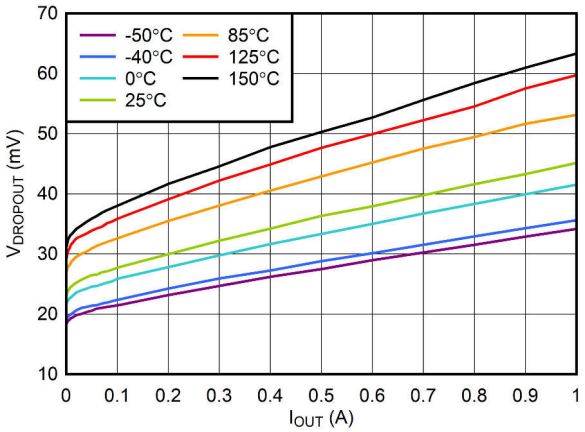
This design example is powered by a rechargeable battery that can be a building block in many portable applications. Noise-sensitive portable electronics require an efficient, small-size solution for their power supply. Traditional LDOs are known for their low efficiency in contrast to low-input, low-output voltage (LILO) LDOs such as the TPS7A14. The use of a bias rail in the TPS7A14 allows the main power path of the LDO to operate at a lower input voltage, thus reducing the voltage drop across the pass transistor and maximizing device efficiency. Because the voltage drop across the pass transistor can be so low, the efficiency of the TPS7A14 can approximate that of a dc-dc converter. 式 8 calculates the efficiency for this design.

$$\text{Efficiency} = \eta = P_{OUT} / P_{IN} \times 100\ \% = (V_{OUT} \times I_{OUT}) / (V_{IN} \times I_{IN} + V_{BIAS} \times I_{BIAS}) \times 100\ \% \quad (8)$$

式 8 reduces to 式 9 because the design example load current is much greater than the quiescent current of the bias rail.

$$\text{Efficiency} = \eta = (V_{OUT} \times I_{OUT}) / (V_{IN} \times I_{IN}) \times 100\% \quad (9)$$

8.2.3 Application Curve



V_{BIAS} = $V_{OUT(NOM)}$ + 1.4 V, V_{EN} = V_{IN}, C_{IN} = 2.2 µF, C_{OUT} = 2.2 µF, and C_{BIAS} = 0.47 µF

図 8-5. V_{IN} Dropout Voltage vs I_{OUT}

8.3 Power Supply Recommendations

This device is designed to operate from an input supply voltage range of 0.6 V to 2.2 V and a bias supply voltage range of 1.5 V to 5.5 V. The input and bias supplies must be well regulated and free of spurious noise. To make sure that the output voltage is well regulated and dynamic performance is optimum, the input supply must be at least $V_{OUT(nom)}$ + V_{DO} and V_{BIAS} = $V_{OUT(nom)}$ + $V_{DO(BIAS)}$.

8.4 Layout

8.4.1 Layout Guidelines

For correct printed circuit board (PCB) layout, follow these guidelines:

- Place input, output, and bias capacitors as close to the device as possible
- Use copper planes for device connections to optimize thermal performance
- Place thermal vias around the device to distribute heat

8.4.2 Layout Examples

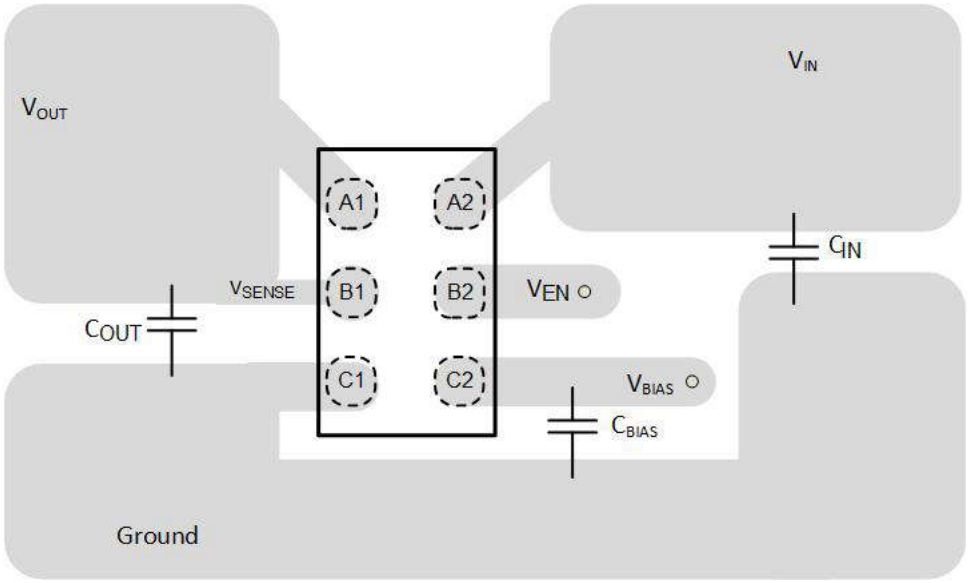


図 8-6. Recommended Layout (YBK Package)

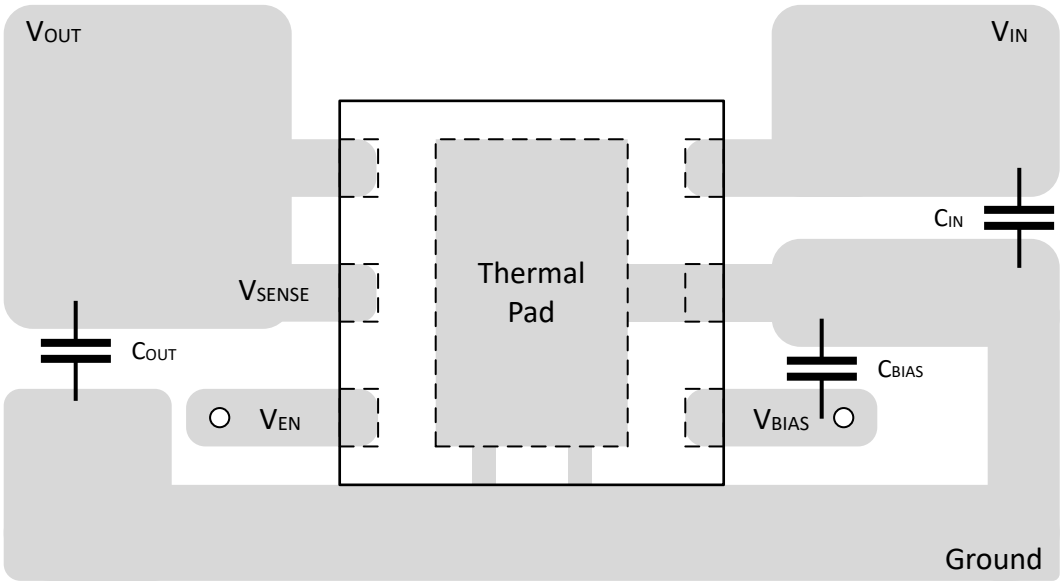


図 8-7. Recommended Layout (DRV Package)

9 Device and Documentation Support

9.1 Device Support

9.1.1 Development Support

9.1.1.1 Evaluation Module

An evaluation module (EVM) is available to assist in the initial circuit performance evaluation using the TPS7A14. The EVM can be requested at the Texas Instruments web site through the product folder or purchased directly from the TI eStore.

9.1.2 Device Nomenclature

表 9-1. Device Nomenclature(1)(2)

PRODUCT	DESCRIPTION
TPS7A14**xx(x)(P)yyyz**	**xx(x)** is the nominal output voltage. Two or more digits are used in the ordering number (for example, 09 = 0.9 V, 95 = 0.95 V, 125 = 1.25 V). **P** indicates active pull down; if there is no P, then the device does not have the active pull down feature. **yyy** is the package designator. **z** is the package quantity. R indicates reel (12000 pieces for YBK package; 3000 pieces for DRV package).

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or visit the device product folder on www.ti.com.
(2) Output voltages from 0.5 V to 2.0 V in 25-mV increments are available. Contact the factory for details and availability.

9.2 Documentation Support

9.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *Using New Thermal Metrics* application report
- Texas Instruments, *AN-1112 DSBGA Wafer Level Chip Scale Package* application report
- Texas Instruments, *TPS7A14EVM-058 Evaluation Module* user guide

9.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

9.4 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の使用条件を参照してください。

9.5 Trademarks

TI E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

9.6 静電気放電に関する注意事項

この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

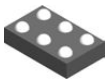
9.7 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

10.1 Mechanical Data

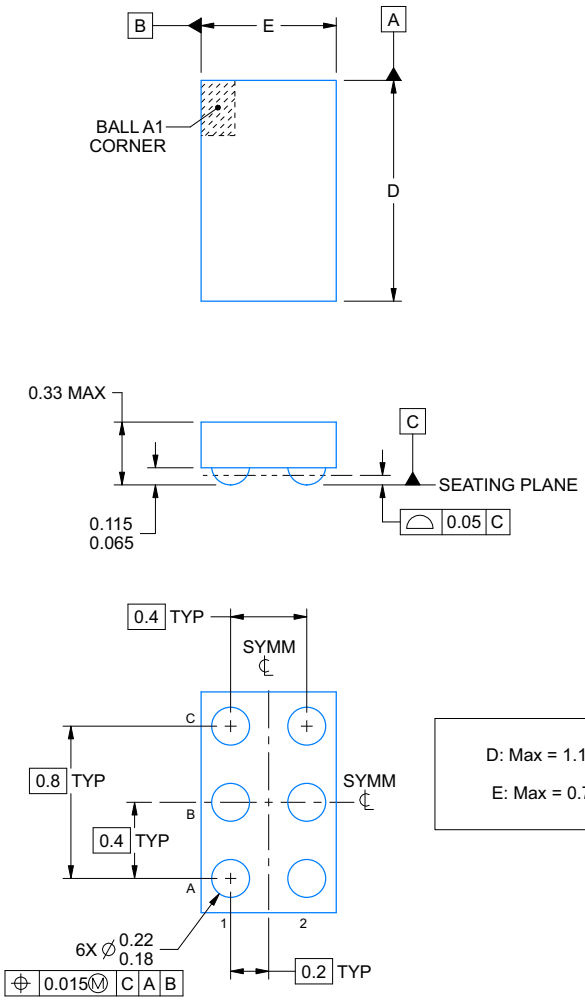


PACKAGE OUTLINE

YBK0006-C02

DSBGA - 0.33 mm max height

DIE SIZE BALL GRID ARRAY



4228735/A 05/2022

NOTES:

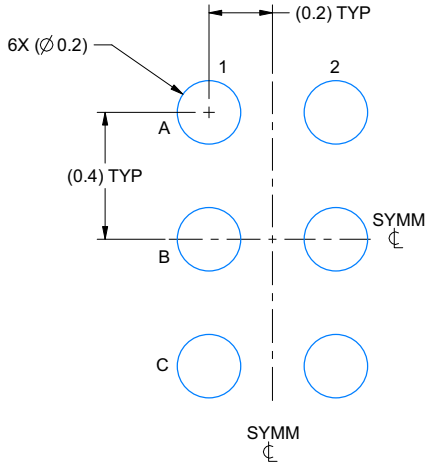
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

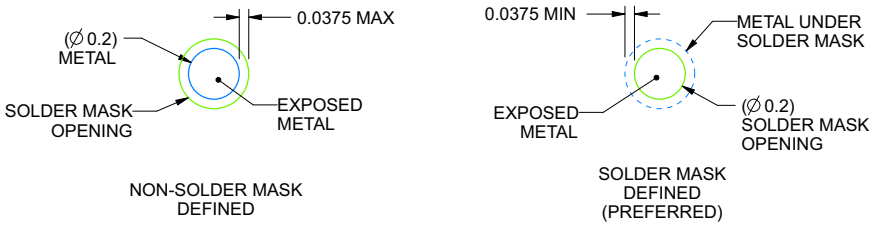
YBK0006-C02

DSBGA - 0.33 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 50X



SOLDER MASK DETAILS
NOT TO SCALE

4228735/A 05/2022

NOTES: (continued)

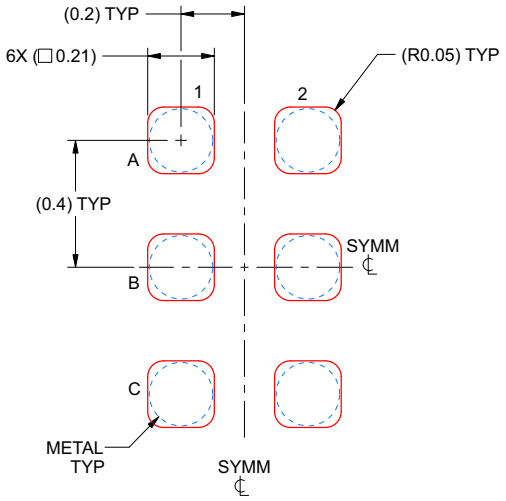
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YBK0006-C02

DSBGA - 0.33 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.075 mm THICK STENCIL
SCALE: 50X

4228735/A 05/2022

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS7A1408PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33PH	Samples
TPS7A1408PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	M8	Samples
TPS7A1409PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33QH	Samples
TPS7A1409PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	MD	Samples
TPS7A14105PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33SH	Samples
TPS7A1410PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33RH	Samples
TPS7A1411PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	P6	Samples
TPS7A1412PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33UH	Samples
TPS7A1412PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	MG	Samples
TPS7A1413PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	MH	Samples
TPS7A1418PDRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	33WH	Samples
TPS7A1485PYBKR	ACTIVE	DSBGA	YBK	6	12000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	M9	Samples
XS7A1408PDRVR	ACTIVE	WSON	DRV	6	3000	TBD	Call TI	Call TI	-40 to 125		Samples
XS7A1418PDRVR	ACTIVE	WSON	DRV	6	3000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

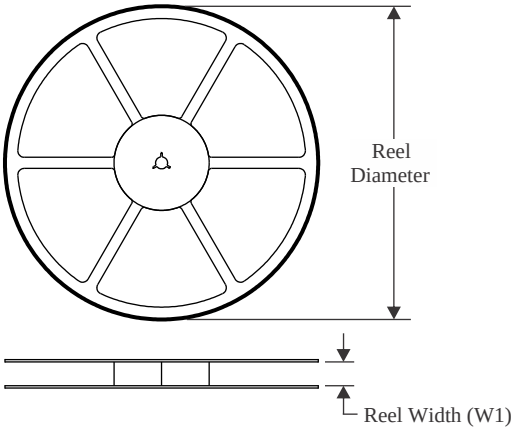
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

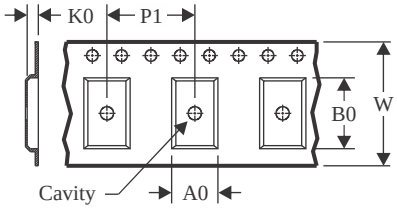
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

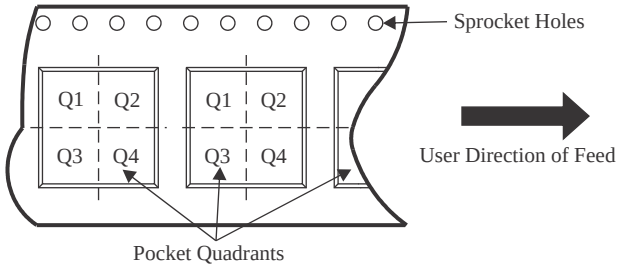


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

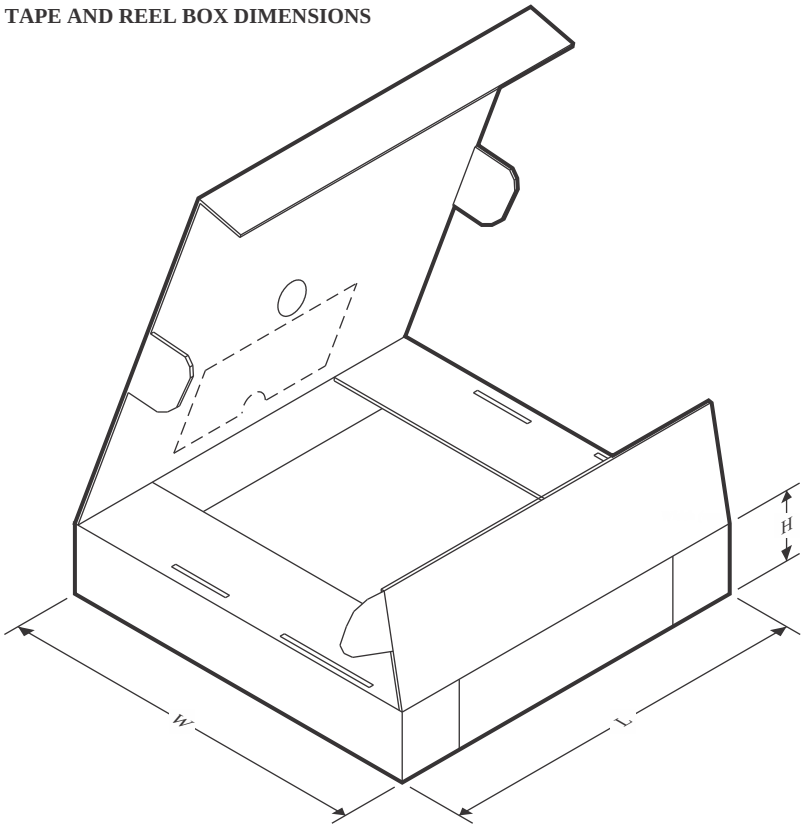


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS7A1408PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1408PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1408PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1409PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1409PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1409PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A14105PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1410PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1411PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1412PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1412PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1412PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1413PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1413PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1
TPS7A1418PDRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS7A1485PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS7A1485PYBKR	DSBGA	YBK	6	12000	180.0	8.4	0.8	1.26	0.36	2.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS7A1408PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1408PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1408PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1409PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1409PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1409PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A14105PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1410PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1411PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1412PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1412PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1412PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1413PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1413PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1418PDRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS7A1485PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0
TPS7A1485PYBKR	DSBGA	YBK	6	12000	182.0	182.0	20.0

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